

Antoine Kahn

List of Publications by Year in descending order

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266
papers

30,839
citations

2696

98
h-index

5347

170
g-index

275
all docs

275
docs citations

275
times ranked

26625
citing authors

#	ARTICLE	IF	CITATIONS
1	Controlled n-Doping of Naphthalene-Imide-Based 2D Polymers. <i>Advanced Materials</i> , 2022, 34, e2101932.	11.1	13
2	Powerful Organic Molecular Oxidants and Reductants Enable Ambipolar Injection in a Large-Gap Organic Homojunction Diode. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 2381-2389.	4.0	5
3	Nonradiative Recombination via Charge-Transfer-Exciton to Polaron Energy Transfer Limits Photocurrent in Organic Solar Cells. <i>Advanced Energy Materials</i> , 2022, 12, .	10.2	5
4	Electrochemically n-Doped CsPbBr ₃ Nanocrystal Thin Films. <i>ACS Energy Letters</i> , 2022, 7, 211-216.	8.8	8
5	Design of UV-Absorbing Donor Molecules for Nearly Imperceptible Organic Solar Cells. <i>ACS Energy Letters</i> , 2022, 7, 180-188.	8.8	14
6	p-Type molecular doping by charge transfer in halide perovskite. <i>Materials Advances</i> , 2021, 2, 2956-2965.	2.6	17
7	Coronene derivatives for transparent organic photovoltaics through inverse materials design. <i>Journal of Materials Chemistry C</i> , 2021, 9, 1310-1317.	2.7	12
8	Direct Probing of Gap States and Their Passivation in Halide Perovskites by High-Sensitivity, Variable Energy Ultraviolet Photoelectron Spectroscopy. <i>Journal of Physical Chemistry C</i> , 2021, 125, 5217-5225.	1.5	12
9	Adduct-based p-doping of organic semiconductors. <i>Nature Materials</i> , 2021, 20, 1248-1254.	13.3	40
10	Molecular dopants: Tools to control the electronic structure of metal halide perovskite interfaces. <i>Applied Physics Reviews</i> , 2021, 8, .	5.5	8
11	Photocurrent deviation from linearity in an organic photodetector due to limited hole transport layer conductivity. <i>Organic Electronics</i> , 2020, 76, 105450.	1.4	7
12	Elucidating the Role of a Tetrafluoroborate-Based Ionic Liquid at the n-Type Oxide/Perovskite Interface. <i>Advanced Energy Materials</i> , 2020, 10, 1903231.	10.2	81
13	Gap States in Methylammonium Lead Halides: The Link to Dimethylsulfoxide?. <i>Advanced Materials</i> , 2020, 32, e2003482.	11.1	21
14	The properties, photovoltaic performance and stability of visible to near-IR all inorganic perovskites. <i>Materials Advances</i> , 2020, 1, 1920-1929.	2.6	5
15	n-Doping of a Low-Electron-Affinity Polymer Used as an Electron-Transport Layer in Organic Light-Emitting Diodes. <i>Advanced Functional Materials</i> , 2020, 30, 2000328.	7.8	22
16	Structural and Electronic Impact of an Asymmetric Organic Ligand in Diammonium Lead Iodide Perovskites. <i>Advanced Energy Materials</i> , 2020, 10, 1903900.	10.2	17
17	Ultraviolet Photoemission Spectroscopy and Kelvin Probe Measurements on Metal Halide Perovskites: Advantages and Pitfalls. <i>Advanced Energy Materials</i> , 2020, 10, 1903252.	10.2	33
18	Interfacial charge-transfer doping of metal halide perovskites for high performance photovoltaics. <i>Energy and Environmental Science</i> , 2019, 12, 3063-3073.	15.6	111

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19	Sensitization of silicon by singlet exciton fission in tetracene. <i>Nature</i> , 2019, 571, 90-94.	13.7	221
20	Quantum Well Energetics of an $n = 2$ Ruddlesden-Popper Phase Perovskite. <i>Advanced Energy Materials</i> , 2019, 9, 1901005.	10.2	25
21	Molecular-Reductant-Induced Control of a Graphene-Organic Interface for Electron Injection. <i>Chemistry of Materials</i> , 2019, 31, 6624-6632.	3.2	15
22	Complexities of Contact Potential Difference Measurements on Metal Halide Perovskite Surfaces. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 890-896.	2.1	24
23	Halide Perovskites: Is It All about the Interfaces?. <i>Chemical Reviews</i> , 2019, 119, 3349-3417.	23.0	404
24	High-Voltage Photogeneration Exclusively via Aggregation-Induced Triplet States in a Heavy-Atom-Free Nonplanar Organic Semiconductor. <i>Advanced Energy Materials</i> , 2019, 9, 1901649.	10.2	4
25	What Limits the Open-Circuit Voltage of Bromide Perovskite-Based Solar Cells?. <i>ACS Energy Letters</i> , 2019, 4, 1-7.	8.8	71
26	The formation of polymer-dopant aggregates as a possible origin of limited doping efficiency at high dopant concentration. <i>Organic Electronics</i> , 2018, 53, 135-140.	1.4	38
27	Characterization of the Valence and Conduction Band Levels of $n = 1$ 2D Perovskites: A Combined Experimental and Theoretical Investigation. <i>Advanced Energy Materials</i> , 2018, 8, 1703468.	10.2	76
28	Impact of unintentional oxygen doping on organic photodetectors. <i>Organic Electronics</i> , 2018, 54, 64-71.	1.4	10
29	Investigation of the High Electron Affinity Molecular Dopant F6-CNNQ for Hole-Transport Materials. <i>Advanced Functional Materials</i> , 2018, 28, 1703780.	7.8	56
30	Ultrasensitive Heterojunctions of Graphene and 2D Perovskites Reveal Spontaneous Iodide Loss. <i>Joule</i> , 2018, 2, 2133-2144.	11.7	39
31	Variable charge transfer state energies at nanostructured pentacene/C60 interfaces. <i>Applied Physics Letters</i> , 2018, 112, 213302.	1.5	12
32	Toward a better understanding of the doping mechanism involved in Mo(tfd-COCF3) ₃ doped PBDTTT-c. <i>Journal of Applied Physics</i> , 2018, 123, 225501.	1.1	5
33	Electronic structure of the CsPbBr ₃ /polytriarylamine (PTAA) system. <i>Journal of Applied Physics</i> , 2017, 121, .	1.1	93
34	Mixed-Halide Perovskites with Stabilized Bandgaps. <i>Nano Letters</i> , 2017, 17, 6863-6869.	4.5	165
35	Beating the thermodynamic limit with photo-activation of n-doping in organic semiconductors. <i>Nature Materials</i> , 2017, 16, 1209-1215.	13.3	139
36	Pairing of near-ultraviolet solar cells with electrochromic windows for smart management of the solar spectrum. <i>Nature Energy</i> , 2017, 2, .	19.8	195

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37	Valence and Conduction Band Densities of States of Metal Halide Perovskites: A Combined Experimentalâ€Theoretical Study. <i>Journal of Physical Chemistry Letters</i> , 2016, 7, 2722-2729.	2.1	333
38	P-doped organic semiconductor: Potential replacement for PEDOT:PSS in organic photodetectors. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	21
39	Impact of a Low Concentration of Dopants on the Distribution of Gap States in a Molecular Semiconductor. <i>Chemistry of Materials</i> , 2016, 28, 2677-2684.	3.2	29
40	Experimental Characterization of Interfaces of Relevance to Organic Electronics. <i>Materials and Energy</i> , 2016, , 159-191.	2.5	2
41	Morphological Tuning of the Energetics in Singlet Fission Organic Solar Cells. <i>Advanced Functional Materials</i> , 2016, 26, 6489-6494.	7.8	24
42	High-Work-Function Molybdenum Oxide Hole Extraction Contacts in Hybrid Organicâ€Inorganic Perovskite Solar Cells. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 31491-31499.	4.0	151
43	Electronically Passivated Holeâ€Blocking Titanium Dioxide/Silicon Heterojunction for Hybrid Silicon Photovoltaics. <i>Advanced Materials Interfaces</i> , 2016, 3, 1600026.	1.9	17
44	Determination of Energy Level Alignment within an Energy Cascade Organic Solar Cell. <i>Chemistry of Materials</i> , 2016, 28, 794-801.	3.2	54
45	Revisiting the Valence and Conduction Band Size Dependence of PbS Quantum Dot Thin Films. <i>ACS Nano</i> , 2016, 10, 3302-3311.	7.3	118
46	Solution-Processed p-Dopant as Interlayer in Polymer Solar Cells. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 9262-9267.	4.0	22
47	Contorted Hexabenzocoronenes with Extended Heterocyclic Moieties Improve Visible-Light Absorption and Performance in Organic Solar Cells. <i>Chemistry of Materials</i> , 2016, 28, 673-681.	3.2	34
48	Fermi level, work function and vacuum level. <i>Materials Horizons</i> , 2016, 3, 7-10.	6.4	615
49	Hybrid Organicâ€Inorganic Perovskites (HOIPs): Opportunities and Challenges. <i>Advanced Materials</i> , 2015, 27, 5102-5112.	11.1	372
50	Dopant controlled trap-filling and conductivity enhancement in an electron-transport polymer. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	57
51	Impact of Blend Morphology on Interface State Recombination in Bulk Heterojunction Organic Solar Cells. <i>Advanced Functional Materials</i> , 2015, 25, 1090-1101.	7.8	29
52	Titanium dioxide/silicon hole-blocking selective contact to enable double-heterojunction crystalline silicon-based solar cell. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	121
53	Investigation of p-dopant diffusion in polymer films and bulk heterojunctions: Stable spatially-confined doping for all-solution processed solar cells. <i>Organic Electronics</i> , 2015, 23, 151-157.	1.4	42
54	Halogenation of a Nonplanar Molecular Semiconductor to Tune Energy Levels and Bandgaps for Electron Transport. <i>Chemistry of Materials</i> , 2015, 27, 1892-1900.	3.2	55

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55	Quantifying the Extent of Contact Doping at the Interface between High Work Function Electrical Contacts and Poly(3-hexylthiophene) (P3HT). <i>Journal of Physical Chemistry Letters</i> , 2015, 6, 1303-1309.	2.1	40
56	Electronic Level Alignment in Inverted Organometal Perovskite Solar Cells. <i>Advanced Materials Interfaces</i> , 2015, 2, 1400532.	1.9	174
57	Low-Temperature Synthesis of a TiO ₂ /Si Heterojunction. <i>Journal of the American Chemical Society</i> , 2015, 137, 14842-14845.	6.6	70
58	Stability of inverted organic solar cells with ZnO contact layers deposited from precursor solutions. <i>Energy and Environmental Science</i> , 2015, 8, 592-601.	15.6	103
59	NiO _x /MoO ₃ Bilayers as Efficient Hole Extraction Contacts in Organic Solar Cells. <i>Advanced Functional Materials</i> , 2014, 24, 701-706.	7.8	65
60	Molecular doping and tuning threshold voltage in 6,13-bis(triisopropylsilylethynyl)pentacene/polymer blend transistors. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	31
61	Impact of Functionalized Polystyrenes as the Electron Injection Layer on Gold and Aluminum Surfaces: A Combined Theoretical and Experimental Study. <i>Israel Journal of Chemistry</i> , 2014, 54, 779-788.	1.0	2
62	Interface energetics in organo-metal halide perovskite-based photovoltaic cells. <i>Energy and Environmental Science</i> , 2014, 7, 1377.	15.6	624
63	Air-Exposure-Induced Gas-Molecule Incorporation into Spiro-MeOTAD Films. <i>Journal of Physical Chemistry Letters</i> , 2014, 5, 1374-1379.	2.1	96
64	Impact of Hole Transport Layer Surface Properties on the Morphology of a Polymer/Fullerene Bulk Heterojunction. <i>Advanced Energy Materials</i> , 2014, 4, 1301879.	10.2	28
65	Chemically Controlled Reversible and Irreversible Extraction Barriers Via Stable Interface Modification of Zinc Oxide Electron Collection Layer in Polycarbazole-based Organic Solar Cells. <i>Advanced Functional Materials</i> , 2014, 24, 4671-4680.	7.8	76
66	Improved Performance in Bulk Heterojunction Organic Solar Cells with a Sol-Gel MgZnO Electron-Collecting Layer. <i>Advanced Energy Materials</i> , 2014, 4, 1400073.	10.2	22
67	Enhanced Charge-Carrier Injection and Collection Via Lamination of Doped Polymer Layers p-Doped with a Solution-Processible Molybdenum Complex. <i>Advanced Functional Materials</i> , 2014, 24, 2197-2204.	7.8	77
68	Tailoring Electron-Transfer Barriers for Zinc Oxide/C ₆₀ Fullerene Interfaces. <i>Advanced Functional Materials</i> , 2014, 24, 7381-7389.	7.8	54
69	Interface dipole engineering at buried organic-organic semiconductor heterojunctions. <i>Organic Electronics</i> , 2014, 15, 2360-2366.	1.4	15
70	Photoinduced Hole Transfer Becomes Suppressed with Diminished Driving Force in Polymer/Fullerene Solar Cells While Electron Transfer Remains Active. <i>Advanced Functional Materials</i> , 2013, 23, 1238-1249.	7.8	101
71	Mechanistic Study on the Solution-Phase n-Doping of 1,3-Dimethyl-2-aryl-2,3-dihydro-1 <i>H</i> -benzimidazole Derivatives. <i>Journal of the American Chemical Society</i> , 2013, 135, 15018-15025.	6.6	202
72	The effect of structural order on solar cell parameters, as illustrated in a SiC-organic junction model. <i>Energy and Environmental Science</i> , 2013, 6, 3272.	15.6	8

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73	Gap states in Pentacene Thin Film Induced by Inert Gas Exposure. <i>Physical Review Letters</i> , 2013, 110, 267602.	2.9	114
74	Electronic structure and carrier transport at laminated polymer homojunctions. <i>Organic Electronics</i> , 2013, 14, 149-155.	1.4	15
75	Effect of Doping Density on the Charge Rearrangement and Interface Dipole at the Molecule-Silicon Interface. <i>Journal of Physical Chemistry C</i> , 2013, 117, 22422-22427.	1.5	13
76	Hole-blocking crystalline-silicon/titanium-oxide heterojunction with very low interface recombination velocity. , 2013, , .		22
77	(Invited) Wide Bandgap Heterojunctions on Crystalline Silicon. <i>ECS Transactions</i> , 2013, 58, 97-105.	0.3	2
78	Hole-blocking titanium-oxide/silicon heterojunction and its application to photovoltaics. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	183
79	Nature of the Interfaces Between Stoichiometric and Under- σ Stoichiometric MoO_3 and 4,4'-dicarbazole-biphenyl: A Combined Theoretical and Experimental Study. <i>Advanced Functional Materials</i> , 2013, 23, 6091-6099.		26
80	Correlation between interface energetics and open circuit voltage in organic photovoltaic cells. <i>Applied Physics Letters</i> , 2012, 101, 233301.	1.5	88
81	Polyvinylpyrrolidone-modified indium tin oxide as an electron-collecting electrode for inverted polymer solar cells. <i>Applied Physics Letters</i> , 2012, 101, 073303.	1.5	26
82	Charge transport across metal/molecular (alkyl) monolayer-Si junctions is dominated by the LUMO level. <i>Physical Review B</i> , 2012, 85, .	1.1	51
83	Solution doping of organic semiconductors using air-stable n-dopants. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	86
84	Passivation of trap states in unpurified and purified C60 and the influence on organic field-effect transistor performance. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	65
85	Low-temperature, solution-processed molybdenum oxide hole-collection layer for organic photovoltaics. <i>Journal of Materials Chemistry</i> , 2012, 22, 3249.	6.7	147
86	Ultralow Doping in Organic Semiconductors: Evidence of Trap Filling. <i>Physical Review Letters</i> , 2012, 109, 176601.	2.9	231
87	A Universal Method to Produce Low-Work Function Electrodes for Organic Electronics. <i>Science</i> , 2012, 336, 327-332.	6.0	1,878
88	Oriented Growth of Al_2O_3 :ZnO Nanolaminates for Use as Electron-Selective Electrodes in Inverted Polymer Solar Cells. <i>Advanced Functional Materials</i> , 2012, 22, 1531-1538.	7.8	47
89	Transition Metal Oxides for Organic Electronics: Energetics, Device Physics and Applications. <i>Advanced Materials</i> , 2012, 24, 5408-5427.	11.1	1,035
90	Photovoltaic efficiency limits and material disorder. <i>Energy and Environmental Science</i> , 2012, 5, 6022.	15.6	166

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91	Energy level alignment in PCDTBT:PC70BM solar cells: Solution processed NiO _x for improved hole collection and efficiency. <i>Organic Electronics</i> , 2012, 13, 744-749.	1.4	135
92	Doping of Organic Electronic Materials using Air-Stable Organometallics. <i>Advanced Materials</i> , 2012, 24, 699-703.	11.1	163
93	Device Characteristics of Bulk-Heterojunction Polymer Solar Cells are Independent of Interfacial Segregation of Active Layers. <i>Chemistry of Materials</i> , 2011, 23, 2020-2023.	3.2	71
94	Annealing Sequence Dependent Open-Circuit Voltage of Inverted Polymer Solar Cells Attributable to Interfacial Chemical Reaction between Top Electrodes and Photoactive Layers. <i>Langmuir</i> , 2011, 27, 11265-11271.	1.6	14
95	Electronic structure of the poly(3-hexylthiophene):indene-C60 bisadduct bulk heterojunction. <i>Journal of Applied Physics</i> , 2011, 110, 043719.	1.1	44
96	Electronic structure of Vanadium pentoxide: An efficient hole injector for organic electronic materials. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	224
97	Evidence for near-Surface NiOOH Species in Solution-Processed NiO _x Selective Interlayer Materials: Impact on Energetics and the Performance of Polymer Bulk Heterojunction Photovoltaics. <i>Chemistry of Materials</i> , 2011, 23, 4988-5000.	3.2	343
98	Soluble fullerene derivatives: The effect of electronic structure on transistor performance and air stability. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	19
99	Modular construction of P3HT/PCBM planar-heterojunction solar cells by lamination allows elucidation of processing-structure-function relationships. <i>Organic Electronics</i> , 2011, 12, 1963-1972.	1.4	18
100	Filled and empty states of alkanethiol monolayer on Au (111): Fermi level asymmetry and implications for electron transport. <i>Chemical Physics Letters</i> , 2011, 511, 344-347.	1.2	46
101	Inverted Organic Solar Cells with Sol-Gel Processed High Work-Function Vanadium Oxide Hole-Extraction Layers. <i>Advanced Functional Materials</i> , 2011, 21, 4776-4783.	7.8	213
102	MoO ₃ Films Spin-Coated from a Nanoparticle Suspension for Efficient Hole-Injection in Organic Electronics. <i>Advanced Materials</i> , 2011, 23, 70-73.	11.1	317
103	Enhanced Efficiency in Plastic Solar Cells via Energy Matched Solution Processed NiO _x Interlayers. <i>Advanced Energy Materials</i> , 2011, 1, 813-820.	10.2	299
104	Electronic structure and band alignment of 9,10-phenanthrenequinone passivated silicon surfaces. <i>Surface Science</i> , 2011, 605, 1308-1312.	0.8	16
105	Silicon surface passivation by an organic overlayer of 9,10-phenanthrenequinone. <i>Applied Physics Letters</i> , 2010, 96, 222109.	1.5	40
106	The Role of Transition Metal Oxides in Charge-Generation Layers for Stacked Organic Light-Emitting Diodes. <i>Advanced Functional Materials</i> , 2010, 20, 1762-1766.	7.8	150
107	The Influence of Film Morphology in High-Mobility Small-Molecule:Polymer Blend Organic Transistors. <i>Advanced Functional Materials</i> , 2010, 20, 2330-2337.	7.8	120
108	Molecules on Si: Electronics with Chemistry. <i>Advanced Materials</i> , 2010, 22, 140-159.	11.1	207

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109	Modification of gold source and drain electrodes by self-assembled monolayer in staggered n- and p-channel organic thin film transistors. <i>Organic Electronics</i> , 2010, 11, 227-237.	1.4	108
110	Direct determination of the electronic structure of the poly(3-hexylthiophene):phenyl-[6,6]-C61 butyric acid methyl ester blend. <i>Organic Electronics</i> , 2010, 11, 1779-1785.	1.4	211
111	Remote doping of a pentacene transistor: Control of charge transfer by molecular-level engineering. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	36
112	The origin of low water vapor transmission rates through Al ₂ O ₃ /ZrO ₂ nanolaminate gas-diffusion barriers grown by atomic layer deposition. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	103
113	Charge generation layers comprising transition metal-oxide/organic interfaces: Electronic structure and charge generation mechanism. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	171
114	Surface and interface states of gallium-polar versus nitrogen-polar GaN: Impact of thin organic semiconductor overlayers. <i>Journal of Applied Physics</i> , 2010, 107, .	1.1	16
115	Electronic Structure and Dynamics at Organic Donor/Acceptor Interfaces. <i>MRS Bulletin</i> , 2010, 35, 443-448.	1.7	40
116	Molecular-scale properties of MoO ₃ -doped pentacene. <i>Physical Review B</i> , 2010, 82, .	1.1	26
117	A Molybdenum Dithiolene Complex as <i>p</i> -Dopant for Hole-Transport Materials: A Multitechnique Experimental and Theoretical Investigation. <i>Chemistry of Materials</i> , 2010, 22, 524-531.	3.2	65
118	Effect of contamination on the electronic structure and hole-injection properties of MoO ₃ /organic semiconductor interfaces. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	175
119	Hg/Molecular Monolayer~Si Junctions: Electrical Interplay between Monolayer Properties and Semiconductor Doping Density. <i>Journal of Physical Chemistry C</i> , 2010, 114, 10270-10279.	1.5	56
120	Phosphine Oxide Derivatives as Hosts for Blue Phosphors: A Joint Theoretical and Experimental Study of Their Electronic Structure. <i>Chemistry of Materials</i> , 2010, 22, 247-254.	3.2	95
121	Electronic band structure and ensemble effect in monolayers of linear molecules investigated by photoelectron spectroscopy. <i>Physical Review B</i> , 2009, 79, .	1.1	16
122	Role of the deep-lying electronic states of MoO ₃ in the enhancement of hole-injection in organic thin films. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	615
123	Isolated molecular dopants in pentacene observed by scanning tunneling microscopy. <i>Physical Review B</i> , 2009, 80, .	1.1	38
124	Influence of chemical doping on the performance of organic photovoltaic cells. <i>Applied Physics Letters</i> , 2009, 94, 203306.	1.5	41
125	Charge transfer at n-doped organic-organic heterojunctions. <i>Journal of Applied Physics</i> , 2009, 105, .	1.1	57
126	Hole Injection in a Model Fluorene~Triarylamine Copolymer. <i>Advanced Functional Materials</i> , 2009, 19, 304-310.	7.8	34

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127	N-doping of pentacene by decamethylcobaltocene. Applied Physics A: Materials Science and Processing, 2009, 95, 7-13.	1.1	45
128	Energetics of metal-organic interfaces: New experiments and assessment of the field. Materials Science and Engineering Reports, 2009, 64, 1-31.	14.8	573
129	P-type doping of organic wide band gap materials by transition metal oxides: A case-study on Molybdenum trioxide. Organic Electronics, 2009, 10, 932-938.	1.4	392
130	Electrical Transport and Photoemission Experiments of Alkylphosphonate Monolayers on GaAs. Journal of Physical Chemistry C, 2009, 113, 3313-3321.	1.5	27
131	Use of a High Electron-Affinity Molybdenum Dithiolene Complex to p-Dope Hole-Transport Layers. Journal of the American Chemical Society, 2009, 131, 12530-12531.	6.6	91
132	Doping Molecular Monolayers: Effects on Electrical Transport Through Alkyl Chains on Silicon. Advanced Functional Materials, 2008, 18, 2102-2113.	7.8	31
133	Electronic Current Transport through Molecular Monolayers: Comparison between Hg/Alkoxy and Alkyl Monolayer/Si(100) Junctions. Advanced Materials, 2008, 20, 3931-3936.	11.1	43
134	Decamethylcobaltocene as an efficient n-dopant in organic electronic materials and devices. Organic Electronics, 2008, 9, 575-581.	1.4	95
135	Improving charge injection in organic thin-film transistors with thiol-based self-assembled monolayers. Organic Electronics, 2008, 9, 419-424.	1.4	112
136	Fluorenyl-substituted silole molecules: geometric, electronic, optical, and device properties. Journal of Materials Chemistry, 2008, 18, 3157.	6.7	41
137	Enhancement of electron injection into a light-emitting polymer from an aluminum oxide cathode modified by a self-assembled monolayer. Applied Physics Letters, 2008, 93, .	1.5	37
138	Commensurate growth and diminishing substrate influence in a multilayer film of a tris(thieno)hexaazatriphenylene derivative on Au(111) studied by scanning tunneling microscopy. Physical Review B, 2008, 77, .	1.1	11
139	Measurements of the Einstein relation in doped and undoped molecular thin films. Physical Review B, 2008, 77, .	1.1	16
140	Substrate-dependent electronic structure of an organic heterojunction. Physical Review B, 2008, 77, .	1.1	30
141	Energy level alignment between 9-phosphonoanthracene self-assembled monolayers and pentacene. Applied Physics Letters, 2007, 90, 012109.	1.5	29
142	Incorporation of cobaltocene as an n-dopant in organic molecular films. Journal of Applied Physics, 2007, 102, 014906.	1.1	36
143	Effect of Doping on Electronic Transport through Molecular Monolayer Junctions. Journal of the American Chemical Society, 2007, 129, 7494-7495.	6.6	27
144	Photoelectron Spectroscopic Study of the Electronic Band Structure of Polyfluorene and Fluorene-Arylamine Copolymers at Interfaces. Journal of Physical Chemistry C, 2007, 111, 1378-1384.	1.5	124

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145	Synthesis, Ionisation Potentials and Electron Affinities of Hexaazatrinaphthylene Derivatives. Chemistry - A European Journal, 2007, 13, 3537-3547.	1.7	88
146	What is the Barrier for Tunneling Through Alkyl Monolayers? Results from n- and p-Si-Alkyl/Hg Junctions. Advanced Materials, 2007, 19, 445-450.	11.1	122
147	Electron spectra of a self-assembled monolayer on gold: Inverse photoemission and two-photon photoemission spectroscopy. Chemical Physics Letters, 2007, 446, 359-364.	1.2	13
148	Induced Density of States model for weakly-interacting organic semiconductor interfaces. Organic Electronics, 2007, 8, 241-248.	1.4	135
149	Threshold voltage as a measure of molecular level shift in organic thin-film transistors. Applied Physics Letters, 2006, 88, 043509.	1.5	25
150	Radiation Damage to Alkyl Chain Monolayers on Semiconductor Substrates Investigated by Electron Spectroscopy. Journal of Physical Chemistry B, 2006, 110, 21826-21832.	1.2	34
151	Electronic structure of Si(111)-bound alkyl monolayers: Theory and experiment. Physical Review B, 2006, 74, .	1.1	103
152	Energy Level and Band Alignment for GaAs-Alkylthiol Monolayer-Hg Junctions from Electrical Transport and Photoemission Experiments. Journal of Physical Chemistry B, 2006, 110, 14363-14371.	1.2	66
153	N-type doping of an electron-transport material by controlled gas-phase incorporation of cobaltocene. Chemical Physics Letters, 2006, 431, 67-71.	1.2	94
154	Spectroscopic study on sputtered PEDOT-PSS: Role of surface PSS layer. Organic Electronics, 2006, 7, 387-396.	1.4	233
155	Doping-induced realignment of molecular levels at organic-organic heterojunctions. Chemical Physics, 2006, 325, 129-137.	0.9	81
156	Molecular n-Type Doping of 1,4,5,8-Naphthalene Tetracarboxylic Dianhydride by Pyronin-B Studied Using Direct and Inverse Photoelectron Spectroscopies. Advanced Functional Materials, 2006, 16, 831-837.	7.8	126
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